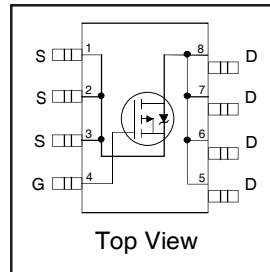


# IRF7404QPbF

HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- P Channel MOSFET
- Surface Mount
- Available in Tape & Reel
- 150°C Operating Temperature
- Lead-Free

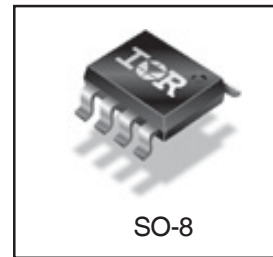


$V_{DSS} = -20V$
$R_{DS(on)} = 0.040\Omega$

## Description

These HEXFET® Power MOSFET's in package utilize the latest processing techniques to achieve extremely low on-resistance per silicon area. Additional features of these HEXFET Power MOSFET's are a 150°C junction operating temperature, fast switching speed and improved repetitive avalanche rating. These benefits combine to make this design an extremely efficient and reliable device for use in a wide variety of applications.

The efficient SO-8 package provides enhanced thermal characteristics making it ideal in a variety of power applications. This surface mount SO-8 can dramatically reduce board space and is also available in Tape & Reel.



## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	10 Sec. Pulsed Drain Current, $V_{GS} @ -4.5V$	-7.7	A
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-6.7	
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	-5.4	
$I_{DM}$	Pulsed Drain Current ①	-27	
$P_D @ T_A = 25^\circ C$	Power Dissipation	2.5	W
	Linear Derating Factor	0.02	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
dv/dt	Peak Diode Recovery dv/dt ②	-5.0	V/ns
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

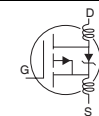
## Thermal Resistance Ratings

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	---	50	°C/W

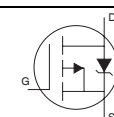
# IRF7404QPbF

International  
**IR** Rectifier

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

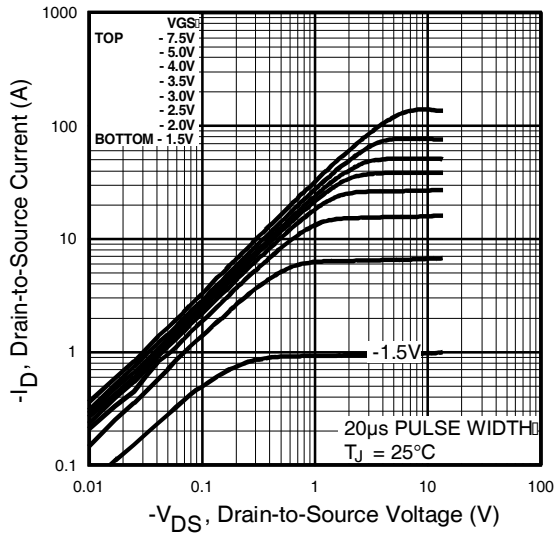
	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
ΔV <sub>(BR)DSS/ΔT<sub>J</sub></sub>	Breakdown Voltage Temp. Coefficient	—	-0.012	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA
R <sub>DS(ON)</sub>	Static Drain-to-Source On-Resistance	—	—	0.040	Ω	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -3.2A ③
		—	—	0.060		V <sub>GS</sub> = -2.7V, I <sub>D</sub> = -2.7A ③
V <sub>GS(th)</sub>	Gate Threshold Voltage	-0.70	—	—	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
g <sub>fs</sub>	Forward Transconductance	6.8	—	—	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -3.2A
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-1.0	μA	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V
		—	—	-25		V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 125°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	-100	nA	V <sub>GS</sub> = -12V
	Gate-to-Source Reverse Leakage	—	—	100		V <sub>GS</sub> = 12V
Q <sub>g</sub>	Total Gate Charge	—	—	50	nC	I <sub>D</sub> = -3.2A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	5.5		V <sub>DS</sub> = -16V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	21		V <sub>GS</sub> = -4.5V, See Fig. 6 and 12 ③
t <sub>d(on)</sub>	Turn-On Delay Time	—	14	—	ns	V <sub>DD</sub> = -10V
t <sub>r</sub>	Rise Time	—	32	—		I <sub>D</sub> = -3.2A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	100	—		R <sub>G</sub> = 6.0Ω
t <sub>f</sub>	Fall Time	—	65	—		R <sub>D</sub> = 3.1Ω, See Fig. 10 ③
L <sub>D</sub>	Internal Drain Inductance	—	2.5	—	nH	Between lead tip and center of die contact 
L <sub>S</sub>	Internal Source Inductance	—	4.0	—		
C <sub>iss</sub>	Input Capacitance	—	1500	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	730	—		V <sub>DS</sub> = -15V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	340	—		f = 1.0MHz, See Fig. 5

## Source-Drain Ratings and Characteristics

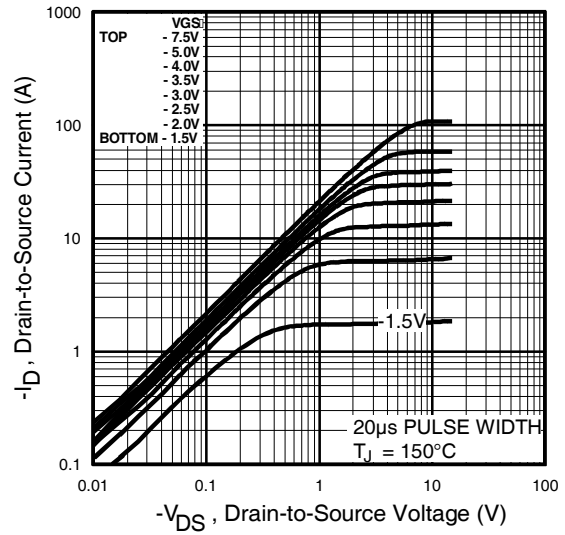
	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-3.1	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	-27		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-1.0	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -2.0A, V <sub>GS</sub> = 0V ③
t <sub>rr</sub>	Reverse Recovery Time	—	69	100	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -3.2A
Q <sub>rr</sub>	Reverse Recovery Charge	—	71	110	μC	di/dt = 100A/μs ③
t <sub>on</sub>	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> +L <sub>D</sub> )				

### Notes:

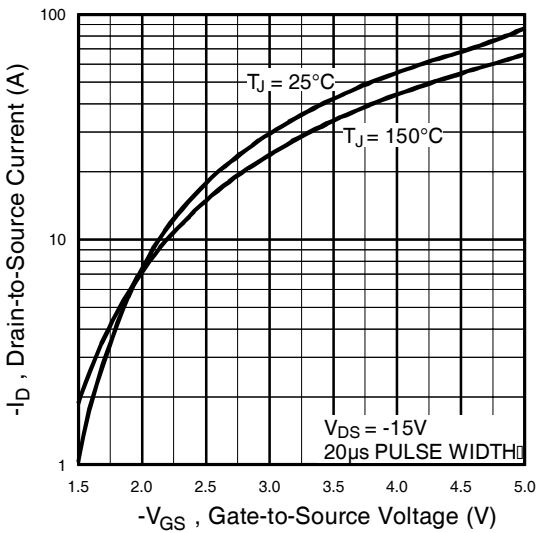
- ① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )
- ② I<sub>SD</sub> ≤ -3.2A, di/dt ≤ -65A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>, T<sub>J</sub> ≤ 150°C
- ③ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ④ Surface mounted on FR-4 board, t ≤ 10sec.



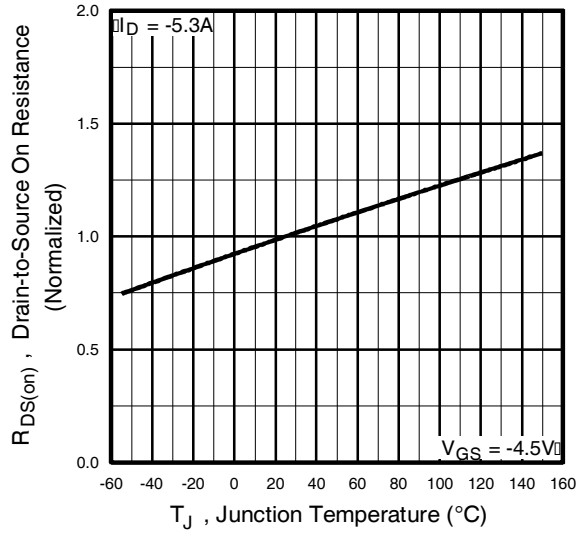
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

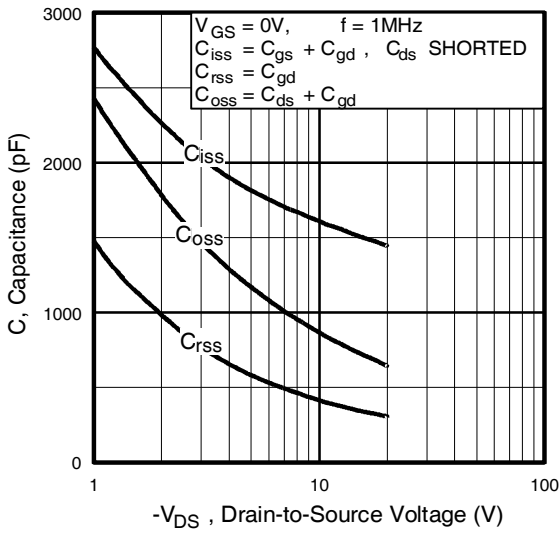


**Fig 3.** Typical Transfer Characteristics

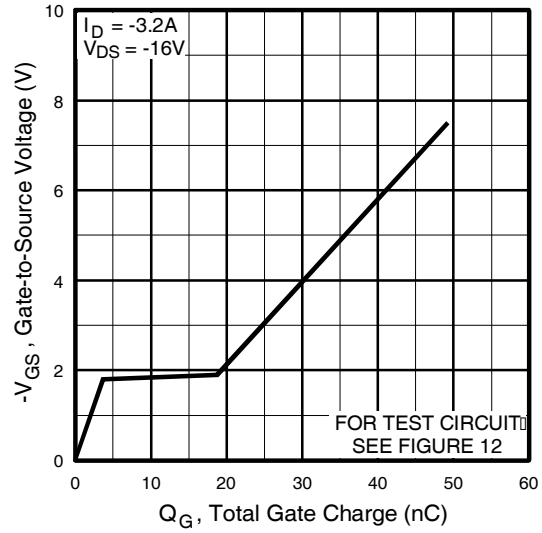


**Fig 4.** Normalized On-Resistance Vs. Temperature

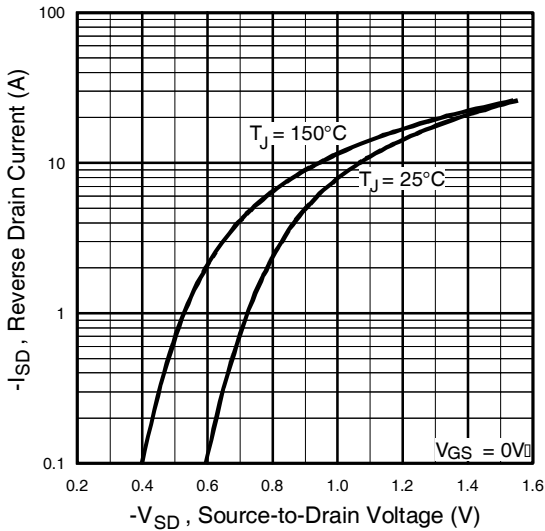
# IRF7404QPbF



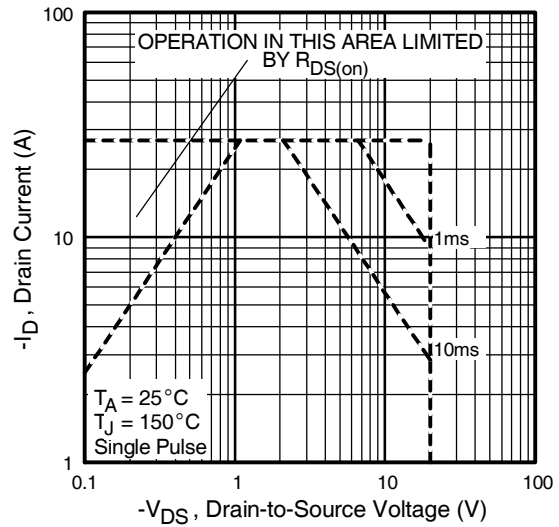
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



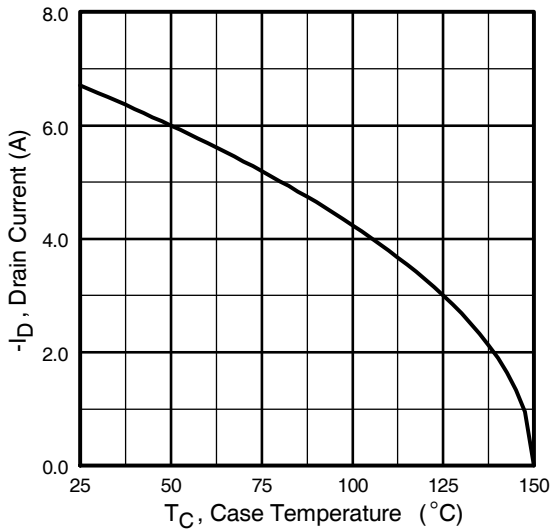
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



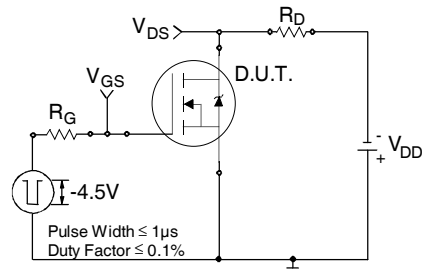
**Fig 7.** Typical Source-Drain Diode Forward Voltage



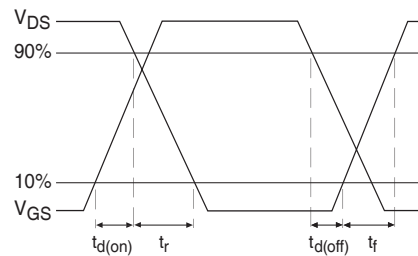
**Fig 8.** Maximum Safe Operating Area



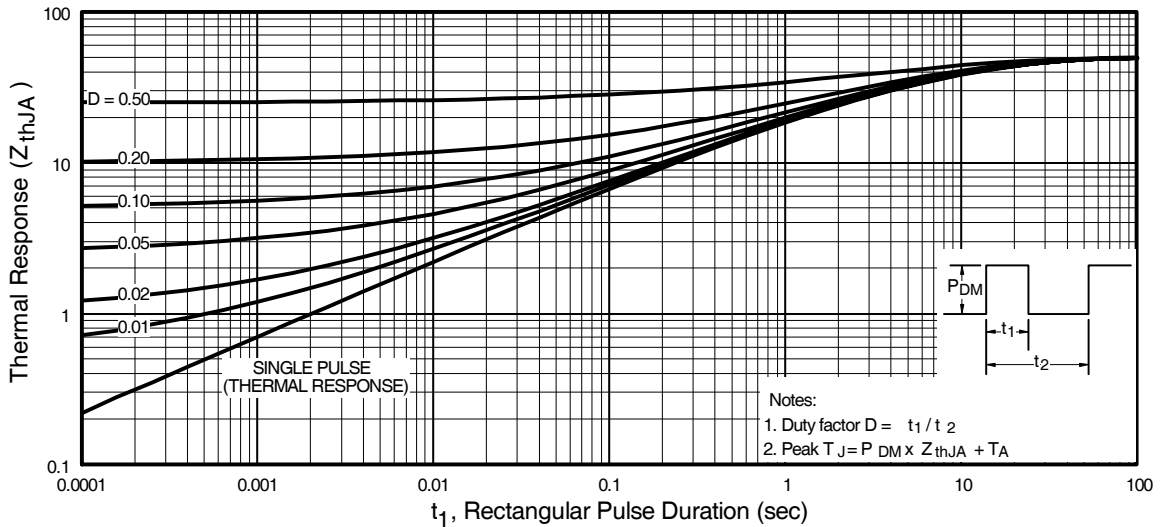
**Fig 9.** Maximum Drain Current Vs. Ambient Temperature



**Fig 10a.** Switching Time Test Circuit

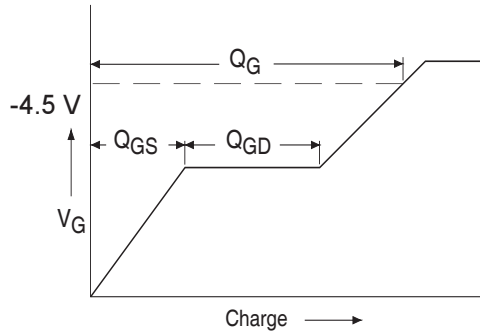


**Fig 10b.** Switching Time Waveforms

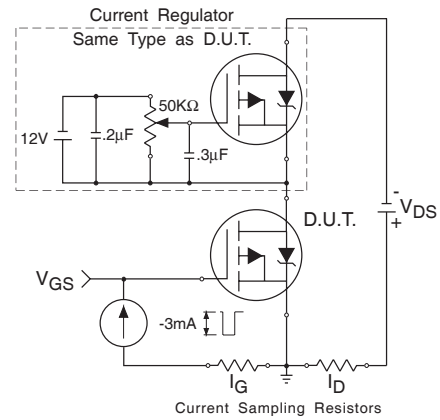


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

# IRF7404QPbF

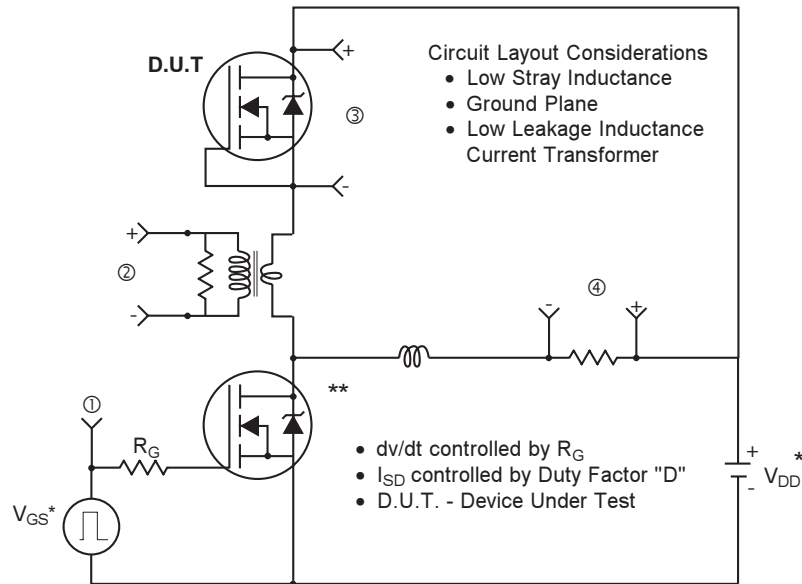


**Fig 12a.** Basic Gate Charge Waveform



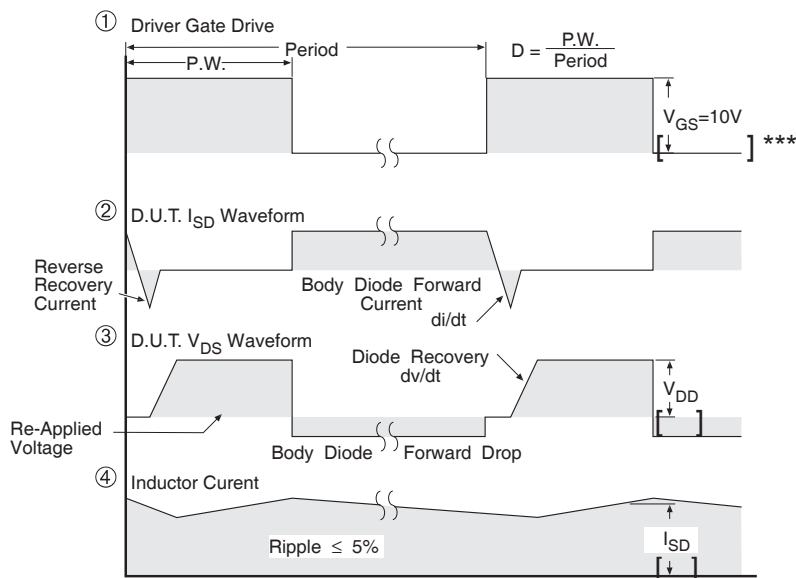
**Fig 12b.** Gate Charge Test Circuit

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity for P-Channel

\*\* Use P-Channel Driver for P-Channel Measurements



\*\*\*  $V_{GS} = 5.0V$  for Logic Level and  $3V$  Drive Devices

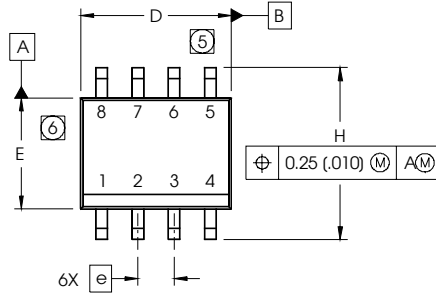
**Fig 13. For P-Channel HEXFETS**

# IRF7404QPbF

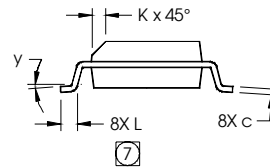
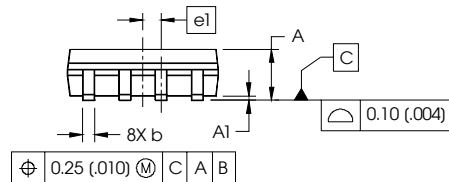
## SO-8 Package Outline

International  
**IR** Rectifier

Dimensions are shown in millimeters (inches)



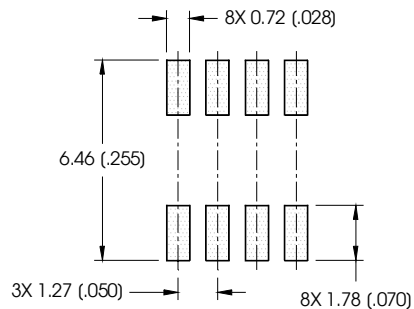
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°



### NOTES:

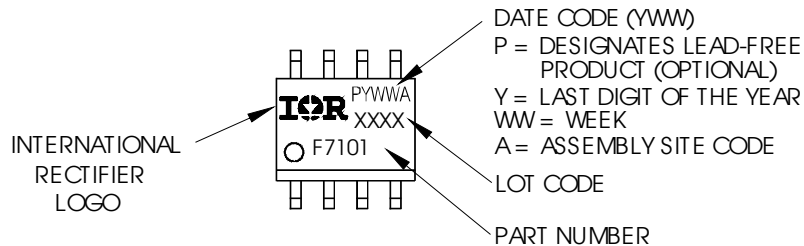
- DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
- CONTROLLING DIMENSION: MILLIMETER
- DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
- OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
- 5** DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
- 6** DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
- 7** DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

### FOOTPRINT



## SO-8 Part Marking

EXAMPLE: THIS IS AN IRF7101 (MOSFET)



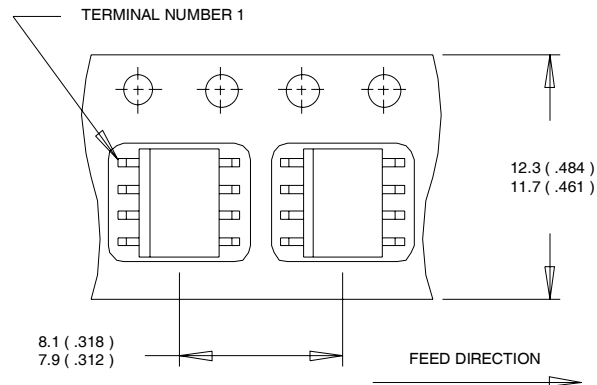
### Notes:

- For an Automotive Qualified version of this part please see <http://www.irf.com/product-info/auto/>
- For the most current drawing please refer to IR website at <http://www.irf.com/package/>



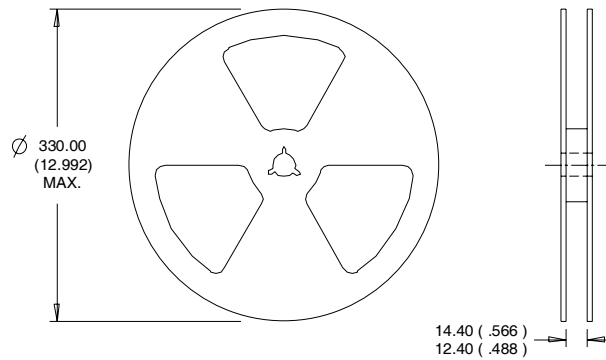
## SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



**NOTES:**

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



**NOTES :**

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.  
 This product has been designed and qualified for the Industrial market.  
 Qualification Standards can be found on IR's Web site.